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# XN0421L (XN421L)

## Silicon NPN epitaxial planar type

### For switching/digital circuits

#### ■ Features

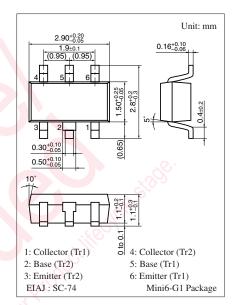
- Two elements incorporated into one package (Transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

#### ■ Basic Part Number

• UNR221L (UN221L) × 2

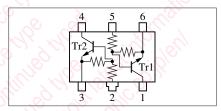
### ■ Absolute Maximum Ratings $T_a = 25$ °C

| Parameter                             | Symbol           | Rating      | Unit |  |
|---------------------------------------|------------------|-------------|------|--|
| Collector-base voltage (Emitter open) | $V_{CBO}$        | 50          | V    |  |
| Collector-emitter voltage (Base open) | V <sub>CEO</sub> | 50          | V    |  |
| Collector current                     | $I_{C}$          | 100         | mA   |  |
| Total power dissipation               | $P_{T}$          | 300         | mW   |  |
| Junction temperature                  | $T_{j}$          | 150         | °C . |  |
| Storage temperature                   | T <sub>stg</sub> | -55 to +150 | °C   |  |



Marking Symbol: DI

#### Internal Connection



### ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

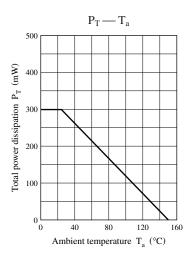
| Parameter                                    | Symbol                          | Conditions   | Min  | Тур | Max  | Unit |
|--|---------------------------------|--|------|-----|------|------|
| Collector-base voltage (Emitter open)        | $V_{CBO}$                       | $I_C = 10 \mu\text{A}, I_E = 0$  | 50   |     |      | V    |
| Collector-emitter voltage (Base open)        | V <sub>CEO</sub>                | $I_C = 2 \text{ mA}, I_B = 0$  | 50   |     |      | V    |
| Collector-base cutoff current (Emitter open) | $I_{CBO}$                       | $V_{CB} = 50 \text{ V}, I_{E} = 0$                                       |      |     | 0.1  | μΑ   |
| Collector-emitter cutoff current (Base open) | $I_{CEO}$                       | $V_{CE} = 50 \text{ V}, I_{B} = 0$                                       |      |     | 0.5  | μΑ   |
| Emitter-base cutoff current (Collector open) | $I_{EBO}$                       | $V_{EB} = 6 \text{ V}, I_C = 0$  |      |     | 2.0  | mA   |
| Forward current transfer ratio               | h <sub>FE</sub>                 | $V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}$                            | 20   |     |      | _    |
| Collector-emitter saturation voltage         | V <sub>CE(sat)</sub>            | $I_C = 10 \text{ mA}, I_B = 0.3 \text{ mA}$                              |      |     | 0.25 | V    |
| Output voltage high-level                    | V <sub>OH</sub>                 | $V_{CC} = 5 \text{ V}, V_B = 0.5 \text{ V}, R_L = 1 \text{ k}\Omega$     | 4.9  |     |      | V    |
| Output voltage low-level                     | V <sub>OL</sub>                 | $V_{CC} = 5 \text{ V}, V_{B} = 2.5 \text{ V}, R_{L} = 1 \text{ k}\Omega$ |      |     | 0.2  | V    |
| Input resistance                             | R <sub>1</sub>                  |  | -30% | 4.7 | +30% | kΩ   |
| Resistance ratio                             | R <sub>1</sub> / R <sub>2</sub> |  | 0.8  | 1.0 | 1.2  | _    |
| Transition frequency                         | $f_T$                           | $V_{CB} = 10 \text{ V}, I_{E} = -2 \text{ mA}, f = 200 \text{ MHz}$      |      | 150 |      | MHz  |

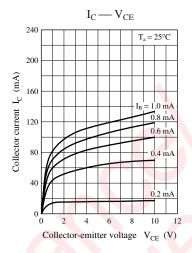
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

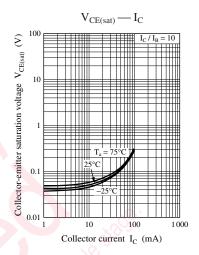
Note) The part number in the parenthesis shows conventional part number.

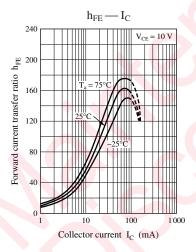
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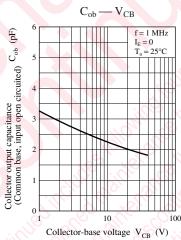
## **Panasonic**

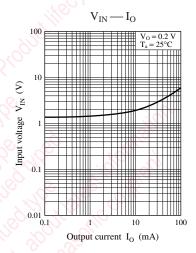












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